Li-Hong Bao

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Construction and physical properties of low-dimensional structures for nanoscale electronic devices. Physical Chemistry Chemical Physics, 2022, 24, 9082-9117.	2.8	3
2	Controllable Synthesis of Atomically Thin 1T‣nSe ₂ Flakes and Its Linear Second Harmonic Generation with Layer Thickness. Advanced Materials Interfaces, 2022, 9, .	3.7	3
3	Ferroelectric-gated ReS2 field-effect transistors for nonvolatile memory. Nano Research, 2022, 15, 5443-5449.	10.4	5
4	Dimensional crossover in self-intercalated antiferromagnetic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi mathvariant="normal">V<mml:mn>5</mml:mn></mml:mi </mml:msub><mml:msub><mml:mi mathvariant="normal">S<mml:mn>8</mml:mn></mml:mi </mml:msub></mml:mrow> nanoflakes. Physical Review B, 2022, 105, .</mml:math 	3.2	6
5	Anomalous thickness dependence of Curie temperature in air-stable two-dimensional ferromagnetic 1T-CrTe2 grown by chemical vapor deposition. Nature Communications, 2021, 12, 809.	12.8	196
6	Intercalation of germanium oxide beneath large-area and high-quality epitaxial graphene on Ir(111) substrate*. Chinese Physics B, 2021, 30, 048102.	1.4	7
7	One-dimensional weak antilocalization effect in 1T′-MoTe2 nanowires grown by chemical vapor deposition. Journal of Physics Condensed Matter, 2021, 33, 185701.	1.8	0
8	Modification of the Interlayer Coupling and Chemical Reactivity of Multilayer Graphene through Wrinkle Engineering. Chemistry of Materials, 2021, 33, 2506-2515.	6.7	10
9	Atomically sharp interface enabled ultrahigh-speed non-volatile memory devices. Nature Nanotechnology, 2021, 16, 882-887.	31.5	105
10	Ultrathin FeTe nanosheets with tetragonal and hexagonal phases synthesized by chemical vapor deposition. Materials Today, 2021, 45, 35-43.	14.2	29
11	A time-shared switching scheme designed for multi-probe scanning tunneling microscope. Review of Scientific Instruments, 2021, 92, 103702.	1.3	2
12	Wrinkle networks in exfoliated multilayer graphene and other layered materials. Carbon, 2020, 156, 24-30.	10.3	23
13	Insulating SiO ₂ under Centimeter-Scale, Single-Crystal Graphene Enables Electronic-Device Fabrication. Nano Letters, 2020, 20, 8584-8591.	9.1	19
14	Local probe of the interlayer coupling strength of few-layers SnSe by contact-resonance atomic force microscopy. Frontiers of Physics, 2020, 15, 1.	5.0	8
15	Ferroelectric-Gated InSe Photodetectors with High On/Off Ratios and Photoresponsivity. Nano Letters, 2020, 20, 6666-6673.	9.1	53
16	Universal mechanical exfoliation of large-area 2D crystals. Nature Communications, 2020, 11, 2453.	12.8	394
17	Wrinkle-induced highly conductive channels in graphene on SiO ₂ /Si substrates. Nanoscale, 2020, 12, 12038-12045.	5.6	11
18	Thickness-Controlled Synthesis of CoX ₂ (X = S, Se, and Te) Single Crystalline 2D Layers with Linear Magnetoresistance and High Conductivity. Chemistry of Materials, 2020, 32, 2321-2329.	6.7	35

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19	Epitaxial growth of metal-semiconductor van der Waals heterostructures NbS2/MoS2 with enhanced performance of transistors and photodetectors. Science China Materials, 2020, 63, 1548-1559.	6.3	40
20	Bipolar Thermoelectrical Transport of SnSe Nanoplate in Low Temperature*. Chinese Physics Letters, 2020, 37, 017301.	3.3	6
21	Transition-Metal Substitution-Induced Lattice Strain and Electrical Polarity Reversal in Monolayer WS ₂ . ACS Applied Materials & Interfaces, 2020, 12, 18650-18659.	8.0	20
22	InSe/hBN/graphite heterostructure for high-performance 2D electronics and flexible electronics. Nano Research, 2020, 13, 1127-1132.	10.4	48
23	Integrated ionic sieving channels from engineering ordered monolayer two-dimensional crystallite structures. Science Bulletin, 2020, 65, 1356-1362.	9.0	3
24	Scalable preparation of water-soluble ink of few-layered WSe ₂ nanosheets for large-area electronics*. Chinese Physics B, 2020, 29, 066802.	1.4	3
25	Electrostatic gating of solid-ion-conductor on InSe flakes and InSe/h-BN heterostructures*. Chinese Physics B, 2020, 29, 118501.	1.4	3
26	Simultaneous generation of direct- and indirect-gap photoluminescence in multilayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"> <mml:msub> <mml:mi>MoS</mml:mi> <mml:mn>2bubbles. Physical Review Materials, 2020, 4, .</mml:mn></mml:msub></mml:math 	าl:mമx <td>ml:m2sub></td>	ml:m2sub>
27	Tin diselenide van der Waals materials as new candidates for mid-infrared waveguide chips. Nanoscale, 2019, 11, 14113-14117.	5.6	4
28	Direct probing of imperfection-induced electrical degradation in millimeter-scale graphene on SiO ₂ substrates. 2D Materials, 2019, 6, 045033.	4.4	2
29	Substrate, a choice of engineering the pseudospin in graphene. 2D Materials, 2019, 6, 045050.	4.4	4
30	Observation of the Kondo Effect in Multilayer Single-Crystalline VTe ₂ Nanoplates. Nano Letters, 2019, 19, 8572-8580.	9.1	52
31	Electronic structure of exfoliated millimeter-sized monolayer WSe2 on silicon wafer. Nano Research, 2019, 12, 3095-3100.	10.4	15
32	Centimeter-scale, single-crystalline, AB-stacked bilayer graphene on insulating substrates. 2D Materials, 2019, 6, 045044.	4.4	11
33	Reversible Modification of Nitrogen-Doped Graphene Based on Se–N Dynamic Covalent Bonds for Field-Effect Transistors. ACS Applied Materials & Interfaces, 2019, 11, 24360-24366.	8.0	13
34	Low-temperature growth of large-scale, single-crystalline graphene on Ir(111)*. Chinese Physics B, 2019, 28, 056107.	1.4	9
35	Quasi-2D Transport and Weak Antilocalization Effect in Few-layered VSe ₂ . Nano Letters, 2019, 19, 4551-4559.	9.1	60
36	Charge-Transfer-Induced Photoluminescence Properties of WSe ₂ Monolayer–Bilayer Homojunction. ACS Applied Materials & Interfaces, 2019, 11, 20566-20573.	8.0	15

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37	Annealing effects on the electrical and photoelectric performance of SnS2 field-effect transistor. Applied Surface Science, 2019, 484, 39-44.	6.1	11
38	Sub-10 nm stable graphene quantum dots embedded in hexagonal boron nitride. Nanoscale, 2019, 11, 4226-4230.	5.6	18
39	One-step solution synthesis of a two-dimensional semiconducting covalent organometallic nanosheet <i>via</i> the condensation of boronic acid. RSC Advances, 2019, 9, 29327-29330.	3.6	2
40	Stable Silicene in Graphene/Silicene Van der Waals Heterostructures. Advanced Materials, 2018, 30, e1804650.	21.0	86
41	Intrinsic charge transport behaviors in graphene-black phosphorus van der Waals heterojunction devices. Chinese Physics B, 2018, 27, 077303.	1.4	4
42	Thick Layered Semiconductor Devices with Water Top-Gates: High On–Off Ratio Field-Effect Transistors and Aqueous Sensors. ACS Applied Materials & Interfaces, 2018, 10, 23198-23207.	8.0	14
43	Upgrade of a commercial four-probe scanning tunneling microscopy system. Review of Scientific Instruments, 2017, 88, 063704.	1.3	13
44	Direct measurements of conductivity and mobility in millimeter-sized single-crystalline graphene via van der Pauw geometry. Chinese Physics B, 2017, 26, 066801.	1.4	14
45	From bidirectional rectifier to polarity-controllable transistor in black phosphorus by dual gate modulation. 2D Materials, 2017, 4, 025056.	4.4	7
46	Direct Four-Probe Measurement of Grain-Boundary Resistivity and Mobility in Millimeter-Sized Graphene. Nano Letters, 2017, 17, 5291-5296.	9.1	59
47	High-quality graphene grown on polycrystalline PtRh20 alloy foils by low pressure chemical vapor deposition and its electrical transport properties. Applied Physics Letters, 2016, 108, .	3.3	3
48	Few-layer SnSe2 transistors with high on/off ratios. Applied Physics Letters, 2016, 108, .	3.3	75
49	Epitaxy of Ultrathin SnSe Single Crystals on Polydimethylsiloxane: Inâ€Plane Electrical Anisotropy and Gateâ€Tunable Thermopower. Advanced Electronic Materials, 2016, 2, 1600292.	5.1	31
50	Introduction of Interfacial Charges to Black Phosphorus for a Family of Planar Devices. Nano Letters, 2016, 16, 6870-6878.	9.1	69
51	Atomic-Scale Imaging of Cation Ordering in Inverse Spinel Zn ₂ SnO ₄ Nanowires. Nano Letters, 2014, 14, 6505-6509.	9.1	19
52	Quantum Corrections Crossover and Ferromagnetism in Magnetic Topological Insulators. Scientific Reports, 2013, 3, 2391.	3.3	43
53	High-quality Bi2Te3 thin films grown on mica substrates for potential optoelectronic applications. Applied Physics Letters, 2013, 103, .	3.3	50
54	A new approach for the preparation of variable valence rare earth alloys from nano rare earth oxides at a low temperature in molten salt. RSC Advances, 2012, 2, 1585-1591.	3.6	9

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55	Aerosol-assisted synthesis of monodisperse single-crystalline α-cristobalite nanospheres. Chemical Communications, 2012, 48, 1293-1295.	4.1	21
56	Weak Anti-localization and Quantum Oscillations of Surface States in Topological Insulator Bi2Se2Te. Scientific Reports, 2012, 2, 726.	3.3	172
57	Towards Textile Energy Storage from Cotton Tâ€Shirts. Advanced Materials, 2012, 24, 3246-3252.	21.0	473
58	Electron Beam Irradiation Stiffens Zinc Tin Oxide Nanowires. Nano Letters, 2011, 11, 4885-4889.	9.1	29
59	Synthesis, structural, optical and mechanical characterization of SrB2O4 nanorods. CrystEngComm, 2011, 13, 5858.	2.6	34
60	Flexible Zn ₂ SnO ₄ /MnO ₂ Core/Shell Nanocableâ^'Carbon Microfiber Hybrid Composites for High-Performance Supercapacitor Electrodes. Nano Letters, 2011, 11, 1215-1220.	9.1	807
61	Core-shell Fe ₃ O ₄ @SiO ₂ nanoparticles synthesized with well-dispersed hydrophilic Fe ₃ O ₄ seeds. Nanoscale, 2011, 3, 701-705.	5.6	284
62	Electric dipolar interaction assisted growth of single crystalline organic thin films. Chinese Physics B, 2010, 19, 067101.	1.4	2
63	Field emission properties of patterned boron nanocones. Nanotechnology, 2010, 21, 325705.	2.6	7
64	Catalyst-Free Synthesis and Structural and Mechanical Characterization of Single Crystalline Ca ₂ B ₂ O ₅ ·H ₂ O Nanobelts and Stacking Faulted Ca ₂ B ₂ O ₅ Nanogrooves. Nano Letters, 2010, 10, 255-262.	9.1	62
65	Patterned boron nanowires and field emission properties. Applied Physics Letters, 2009, 94, .	3.3	17
66	Fabrication of Vertically Aligned Singleâ€Crystalline Boron Nanowire Arrays and Investigation of Their Fieldâ€Emission Behavior. Advanced Materials, 2008, 20, 2609-2615.	21.0	99
67	Self-assembled synthesis of SERS-active silver dendrites and photoluminescence properties of a thin porous silicon layer. Electrochemistry Communications, 2008, 10, 625-629.	4.7	89
68	Large-Scale Fe ₃ O ₄ Nanoparticles Soluble in Water Synthesized by a Facile Method. Journal of Physical Chemistry C, 2008, 112, 11336-11339.	3.1	264
69	Monodisperse Noble-Metal Nanoparticles and Their Surface Enhanced Raman Scattering Properties. Chemistry of Materials, 2008, 20, 6939-6944.	6.7	181
70	Boron Carbide and Silicon Oxide Hetero-nanonecklaces via Temperature Modulation. Crystal Growth and Design, 2008, 8, 3160-3164.	3.0	15
71	Boron nanowires for flexible electronics. Applied Physics Letters, 2008, 93, .	3.3	33
72	A new route to single crystalline vanadium dioxide nanoflakes via thermal reduction. Journal of Materials Research, 2007, 22, 1921-1926.	2.6	15

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73	Large scale SiCâ^•SiOx nanocables: Synthesis, photoluminescence, and field emission properties. Journal of Applied Physics, 2007, 102, .	2.5	35
74	Single Crystalline Boron Nanocones: Electric Transport and Field Emission Properties. Advanced Materials, 2007, 19, 4480-4485.	21.0	80
75	Laser-induced phase conversion of n-type SnSe2 to p-type SnSe. Chinese Physics B, 0, , .	1.4	3